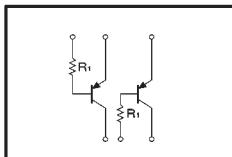


General purpose (dual digital transistors)

IMB7A

Features

- 1) Two DTA143T chips in a SMT package.

Circuit diagram**Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	300 (TOTAL)	mW *
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-55~+150	°C

* 200mW per element must not be exceeded.

Package, marking, and packaging specifications

Part No.	IMB7A
Package	SMT6
Marking	B7
Code	T110
Basic ordering unit (pieces)	3000

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	-50	—	—	V	I _C =-50 μA
Collector-emitter breakdown voltage	BV _{CED}	-50	—	—	V	I _C =-1mA
Emitter-base breakdown voltage	BV _{EBO}	-5	—	—	V	I _E =-50 μA
Collector cutoff current	I _{CBO}	—	—	-0.5	μA	V _{Ce} =-50V
Emitter cutoff current	I _{EBO}	—	—	-0.5	μA	V _{EB} =-4V
DC current transfer ratio	h _{FE}	100	250	600	—	V _{Ce} /I _C =-5V/-1mA
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.3	V	I _C /I _B =-5mA/-0.25mA
Input resistance	R _I	3.29	4.7	6.11	kΩ	—

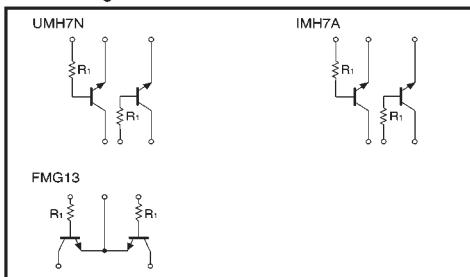
(94S-849-A143T)

General purpose (dual digital transistors)

UMH7N / FMG13 / IMH7A

Features

- 1) Includes two DTA143T transistors in a single UMT package.

Circuit diagram**Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CED}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA
Collector power dissipation	P _C	150 (TOTAL) 300 (TOTAL)	mW *1 *2
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-55~+150	°C

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

Package, marking, and packaging specifications

Part No.	UMH7N	FMG13	IMH7A
Package	UMT6	SMT5	SMT6
Marking	H7	G13	H7
Code	TR	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	50	—	—	V	I _C =50 μA
Collector-emitter breakdown voltage	BV _{CED}	50	—	—	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EBO}	5	—	—	V	I _E =50 μA
Collector cutoff current	I _{CBO}	—	—	0.5	μA	V _{Ce} =50V
Emitter cutoff current	I _{EBO}	—	—	0.5	μA	V _{EB} =4V
DC current transfer ratio	h _{FE}	100	250	600	—	V _{Ce} /I _C =5V/1mA
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.3	V	I _C /I _B =5mA/0.25mA
Input resistance	R _I	3.29	4.7	6.11	kΩ	—

(94S-877-C143T)